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Applicant: MANABE et al.

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Examiner: S. Mulpuri

Group Art Unit: 2812

U.S. PATENT DOCUMENTS

| Examiner's Initials* | Document Number | Date MM/YYYY | Name (Family Name of First Inventor) | Class | Sub Class | Filing Date (if appropriate) |
|-------------------------|--------------------|-----------------|---|-------|--------------|------------------------------------|
| | AR | | | | | |
| | BR | | | | | |
| | CR | | | | | |
| | DR | | | | | |
| | ER | | | | | |
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| | IR | | | | | |
| | JR | | | | | |

FOREIGN PATENT DOCUMENTS

| | Document Number | Date MM/YYYY | Country | Inventor Name | English Abstract | | Translation Readily Available | |
|----|--------------------|-----------------|---------|------------------|---------------------|----|-------------------------------------|----|
| | | | | | Enclosed | No | Enclose | No |
| GM | KR 59-228776 | 12/1984 | Japan | Maefutsu et al. | | X | FULL | |
| GM | LR 56-080183 | 07/1981 | Japan | Kobayashi et al. | X | | | X |
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| | RR | | | | | | | |

OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.)

| | | | | | | | | | |
|----|----|---|--|--|--|--|---|---------|--|
| GM | SR | Amano, <i>The Research on MOVPE Growth and Application to Photoelectric Physical Property of GaN and a Device Emitting Blue-Color Lights</i> , Doctoral Dissertation of Nagoya University, Chapter 7.8 (pages 80-94), January 13, 1989 | | | | | X | Partial | |
| | TR | Jacob et al., <i>Efficient Injection Mechanism for Electroluminescence in GaN</i> , Applied Physics Letter, Vol. 30, No. 8, pp. 412-414, April 15, 1977 | | | | | | | |
| | UR | Tietjen et al., <i>Vapor Phase Growth Technique and System for Several III-V Compound Semiconductors</i> , RCA Laboratories, 5 pages, March 1969 | | | | | X | Partial | |
| | VR | Ta, <i>Photoluminescence Characterization of Shallow Impurities in GaN Grown by Chemical Vapor Deposition</i> , Dissertation for University of Southern California, pages 1-166, July 1981 | | | | | | | |
| | WR | Wang, <i>Photoluminescence and Stimulated Emission from GaN</i> , Dissertation for University of Southern California, pages 1-158, November 1978 | | | | | | | |
| GM | XR | Sayyah, <i>A Study of Growth Mechanisms and Electrical and Optical Properties of Epitaxial Al_{0.15}Ga_{0.85}N layers Grown by Atmospheric Pressure Metalorganic Chemical Vapor Deposition</i> , Dissertation for University of Southern California, pp. 1-176, February 1986 | | | | | | | |

Examiner

Date Considered: 2/8/01

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.